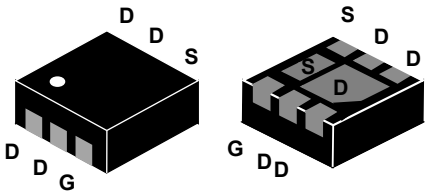
GOOD-ARK SEMICONDUCTOR

GSFB0608

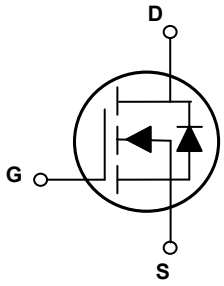
65V N-Channel MOSFET

Main Product Characteristics

BV_{DSS}	65V
$R_{DS(ON)}$	17.4mΩ
I_D	7A



DFN2x2-6L 2EP



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSFB0608 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	+20/-12	V
Drain Current-Continuous (T_A=25°C)	I_D	7.0	A
Drain Current-Continuous (T_A=70°C)		5.6	
Drain Current-Pulsed[1]	I_{DM}	28	A
Power Dissipation (T_A=25°C)	P_D	2	W
Power Dissipation-Derate above 25°C		0.016	W/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	65	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V, T_J=25°C	-	-	1	μA
		V_{DS}=48V, V_{GS}=0V, T_J=85°C	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Static Drain-Source On-Resistance[3]	$R_{DS(ON)}$	V_{GS}=10V, I_D=2A	-	14.5	17.4	mΩ
		V_{GS}=4.5V, I_D=1.5A	-	24	31	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250uA	1.2	1.6	2.5	V
Forward Transconductance	g_{fs}	V_{DS}=10V, I_D=1A	-	3	-	S
Dynamic and Switching Characteristics						
Total Gate Charge[2,3]	Q_g	V_{DS}=30V, I_D=4A V_{GS}=10V	-	10.9	22	nC
Gate-Source Charge[2,3]	Q_{gs}		-	1.5	3	
Gate-Drain Charge[2,3]	Q_{gd}		-	4.4	9	
Turn-On Delay Time[2,3]	$t_{d(on)}$	V_{DD}=30V, R_G=6Ω V_{GS}=10V, I_D=4A	-	8	16	nS
Rise Time[2,3]	t_r		-	12	24	
Turn-Off Delay Time[2,3]	$t_{d(off)}$		-	25	50	
Fall Time[2,3]	t_f		-	18	36	
Input Capacitance	C_{iss}	V_{DS}=30V, V_{GS}=0V, F=1MHz	-	653	1300	pF
Output Capacitance	C_{oss}		-	192	380	
Reverse Transfer Capacitance	C_{rss}		-	27	60	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	-	0.8	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	-	-	7	A
Pulsed Source Current[3]	I_{SM}		-	-	14	A
Diode Forward Voltage[3]	V_{SD}	V_{GS}=0V, I_S=1A, T_J=25°C	-	-	1	V
Reverse Recovery Time	t_{rr}	V_R=50V, I_S=4A di/dt=100A/μs T_J=25°C	-	30	-	nS
Reverse Recovery Charge	Q_{rr}		-	15	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. Pulse test: pulse width ≤ 300us, duty cycle≤ 2%.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

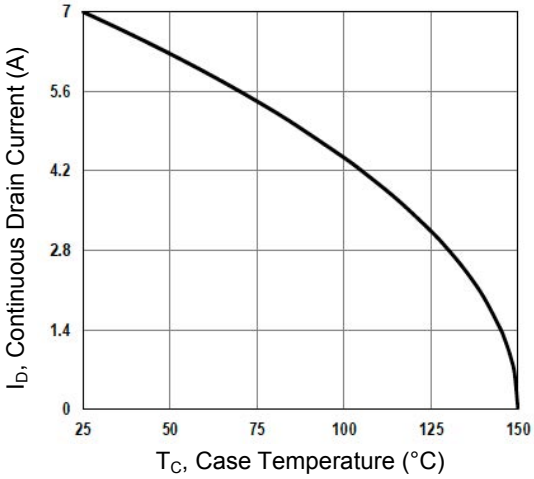


Figure 1. Continuous Drain Current vs. T_C

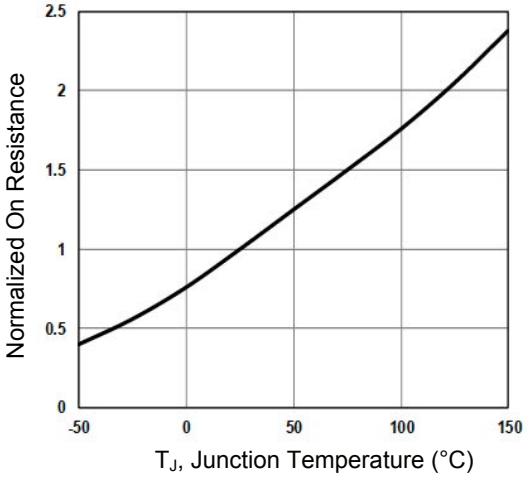


Figure 2. Normalized R_{DSON} vs. T_J

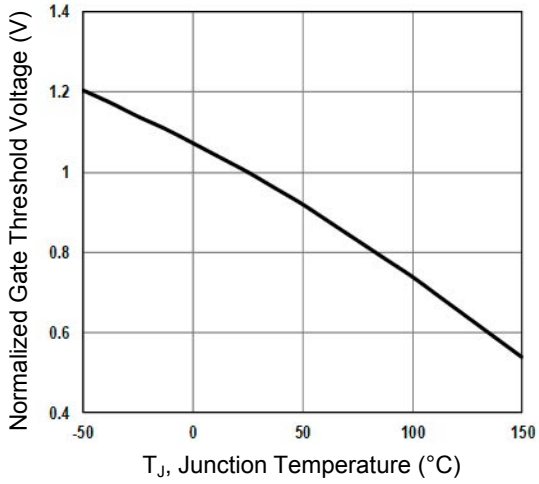


Figure 3. Normalized V_{th} vs. T_J

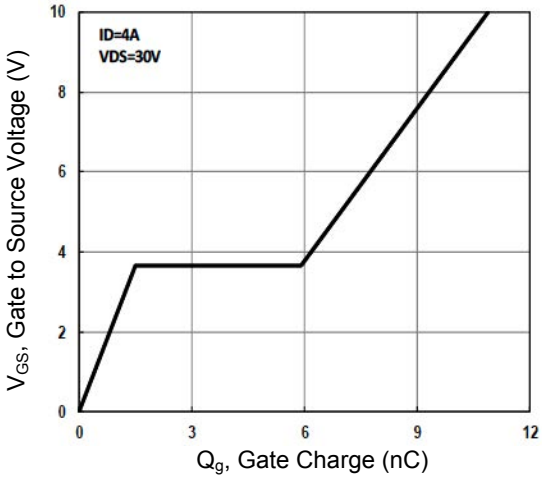


Figure 4. Gate Charge Characteristics

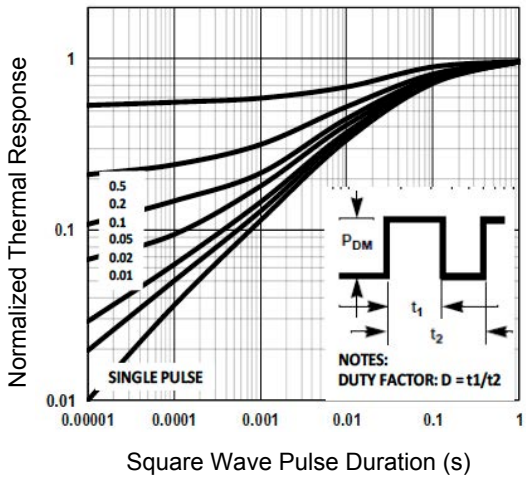


Figure 5. Normalized Transient Impedance

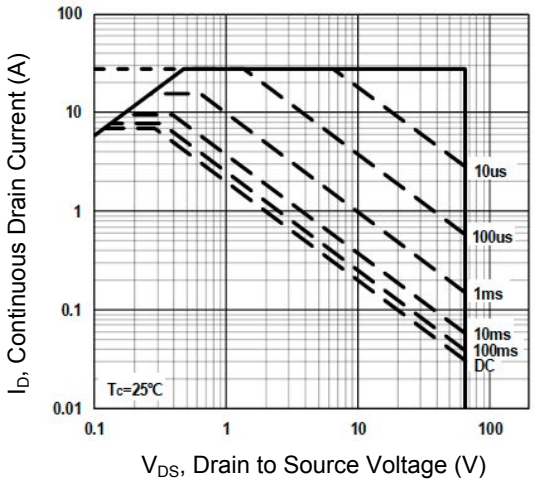


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

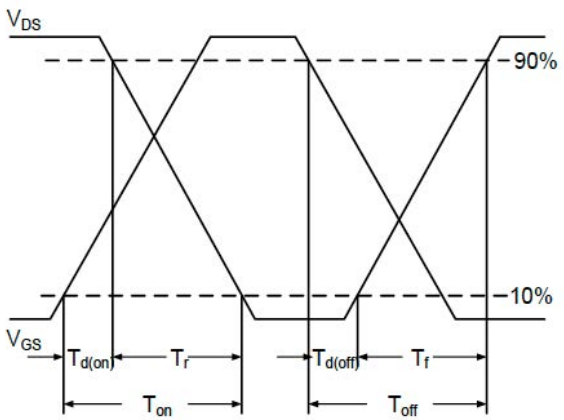


Figure 7. Switching Time Waveform

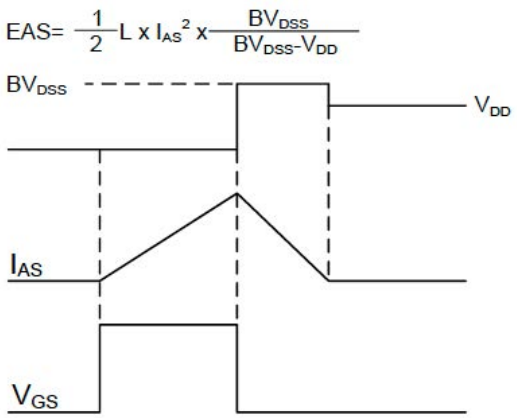
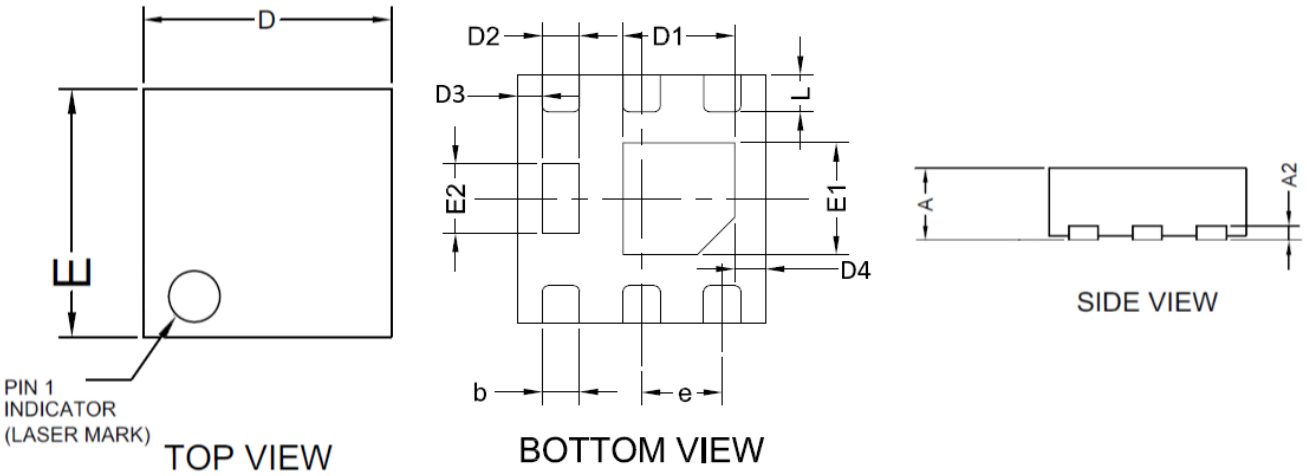


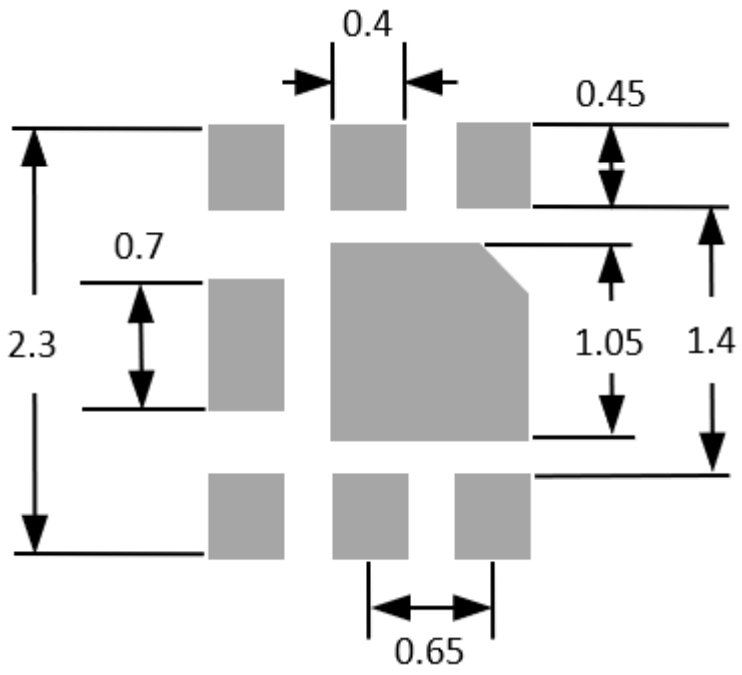
Figure 8. EAS Waveform

Package Outline Dimensions DFN2x2-6L 2EP



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.500	0.800	0.019	0.031
A2	0.145	0.250	0.006	0.010
b	0.250	0.350	0.010	0.014
D	1.900	2.100	0.075	0.083
D1	0.800	1.000	0.031	0.040
D2	0.250	0.350	0.010	0.014
D3	0.200 BSC		0.008 BSC	
D4	0.200 BSC		0.008 BSC	
E	1.900	2.100	0.075	0.083
E1	0.800	1.050	0.031	0.041
E2	0.460	0.660	0.018	0.026
e	0.650 BSC		0.026 BSC	
L	0.250	0.350	0.010	0.014

Recommended Pad Layout



Unit: mm